

Micron Introduces Industry's Highest Density DDR3 Components and Modules

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Boise, Idaho, Tuesday, October 30, 2007 – Building on its heritage of innovation in DRAM technology, Micron Technology, Inc., today announced the industry's first 2 gigabit (Gb) double data rate (DDR) 3 component. Micron's newest DRAM innovation is the highest density DDR3 component available on the market.

By using 2Gb components, Micron can enable 8 gigabyte (GB) and 16GB modules for servers and 4GB modules for desktop and notebook PCs, which are the industry's highest density DDR3 modules available. This increase in memory density is ideal for optimizing today's memory intensive operating systems. Micron is now sampling modules based on its 2Gb DDR3 component for server, desktop and notebook applications. Commercial availability for the product is planned for the first quarter of 2008.

"The graphic intensive features and functionalities designed into today's new operating systems are requiring more and more memory to perform at optimal levels," said Shane Rau, program director for computing, networking and storage semiconductors at IDC. "IDC forecasts that, by the fourth quarter of 2008, the average desktop PC will contain nearly 2.1GBs of DRAM, the average mobile PC over 1.8GBs, and the average x86 server over 11.2GBs."

Micron's 78 nanometer (nm) 2Gb DDR3 memory technology provides increased speeds of up to 1333 megabits per second (Mbps), enabling better system and graphics performance, which provides for a more interactive user experience. For example, when operating at peak performance, DDR3 can transfer a 100,000-page document in approximately one second. And by reducing supply voltage from 1.8 volts to 1.5 volts, Micron's 2Gb DDR3 provides a 20-30 percent memory power savings when compared to DDR2 technology. Further memory power savings can also be realized by using fewer components on a module, approximately 40 to 50 percent depending on module form factor. Reduced memory power consumption can save money on cooling costs in data center server systems and prolong battery life in notebook applications.

"Just as we led the market last year with the introduction of our 1Gb DDR3 component, we are leading the market yet again with our new 2Gb component," said Brian Shirley, vice president of Micron's memory group. "As power consumption continues to be a top concern in the technology industry, Micron remains the leader in the energy-efficient memory movement. It's important that we show customers opportunities for them to reduce memory power consumption. In addition to the reduced core voltage of DDR3, our new 2Gb component allows customers to lower their overall system memory power consumption by using less chips on a module."

About Micron

Micron Technology, Inc., is one of the world's leading providers of advanced semiconductor solutions. Through its worldwide operations, Micron manufactures and markets DRAMs, NAND flash memory, CMOS image sensors, other semiconductor components, and memory modules for use in leading-edge computing, consumer, networking, and mobile products. Micron's common stock is traded on the New York Stock Exchange (NYSE) under the MU symbol. To learn more about Micron Technology, Inc., visit www.micron.com.

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This press release contains forward-looking statements regarding the production of DDR3 memory. Actual events or results may differ materially from those contained in the forward-looking statements. Please refer to the documents the Company files on a consolidated basis from time to time with the Securities and Exchange Commission, specifically the Company's most recent Form 10-K and Form 10-Q. These documents contain and identify important factors that could cause the actual results for the Company on a consolidated basis to differ materially from those contained in our forward-looking statements (see Certain Factors). Although we believe that the expectations reflected in the forward-looking statements are reasonable, we cannot guarantee future results, levels of activity, performance or achievements. We are under no duty to update any of the forward-looking statements after the date of this press release to conform to actual results.

Related Links

Micron Media Center Micron DDR3

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